

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE4080 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

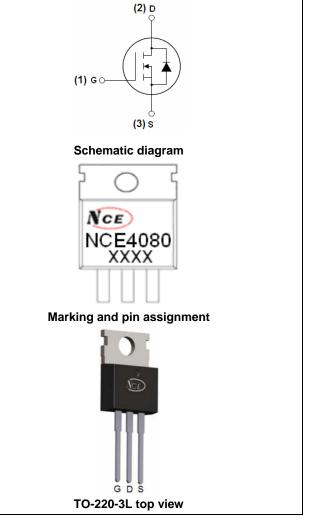
- V_{DS} =40V,I_D =80A
- R_{DS(ON)} <6.5mΩ @ V_{GS}=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

Application

- PWM
- Load Switching

100% UIS TESTED!

100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4080	NCE4080	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	40	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	80	А	
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	56	А	
Pulsed Drain Current	I _{DM}	350	А	
Maximum Power Dissipation	PD	90	W	
Derating factor		0.6	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	670	mJ	
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C	





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.67	°C/W

Electrical Characteristics (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	5.3	6.5	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	<u>)</u> () () () () () () () () () () () () ()	-	4010	-	PF
Output Capacitance	Coss		-	750	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHZ	-	390	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	tr	V_{DD} =20V, R _L =1 Ω	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{DS} =10V,I _D =20A 	-	38	-	nS
Turn-Off Fall Time	t _f		-	11	-	nS
Total Gate Charge	Qg	N/ 001/1 00A	-	50	-	nC
Gate-Source Charge	Q _{gs}		-	12	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	13	-	nC
Drain-Source Diode Characteristics						L
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =10A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	80	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	33	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	34	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negl	igible (turi	n-on is do	minated b	y LS+LD)

Notes:

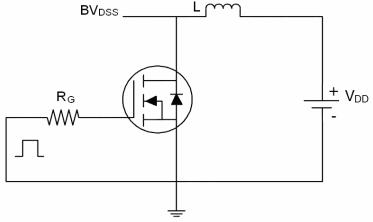
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition : Tj=25 $^{\circ}$ C, V_{DD} =20V, V_{G} =10V, L=1mH, Rg=25 Ω , I_{AS} =36A



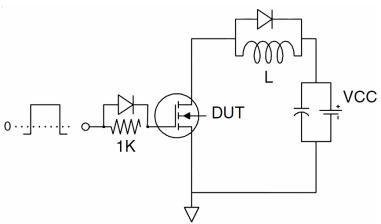
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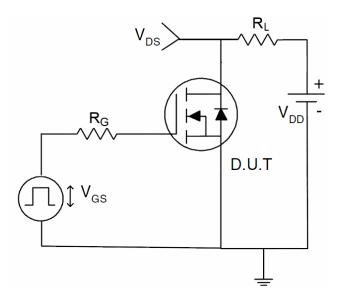
Test circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



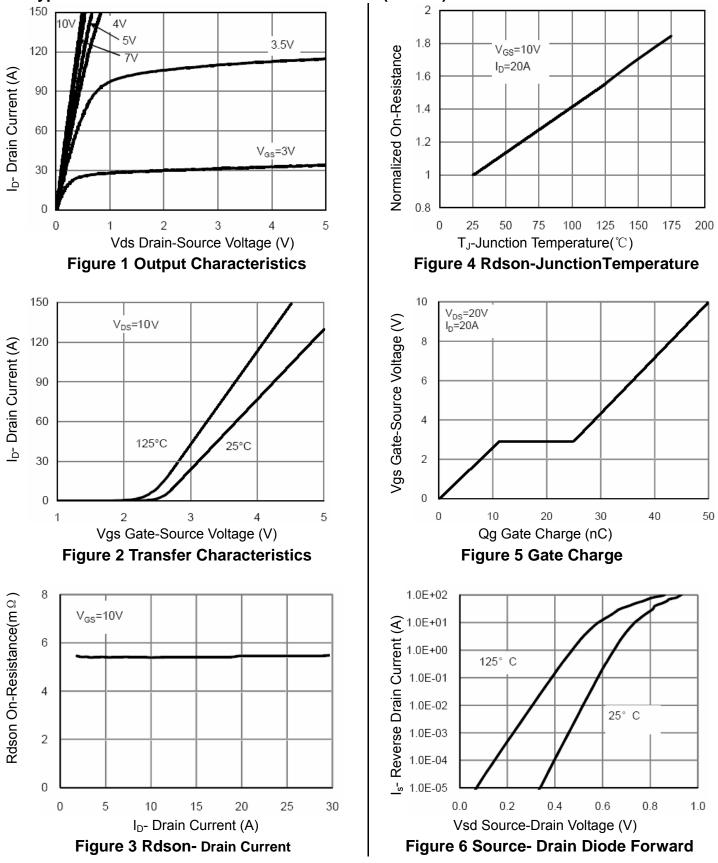
3) Switch Time Test Circuit







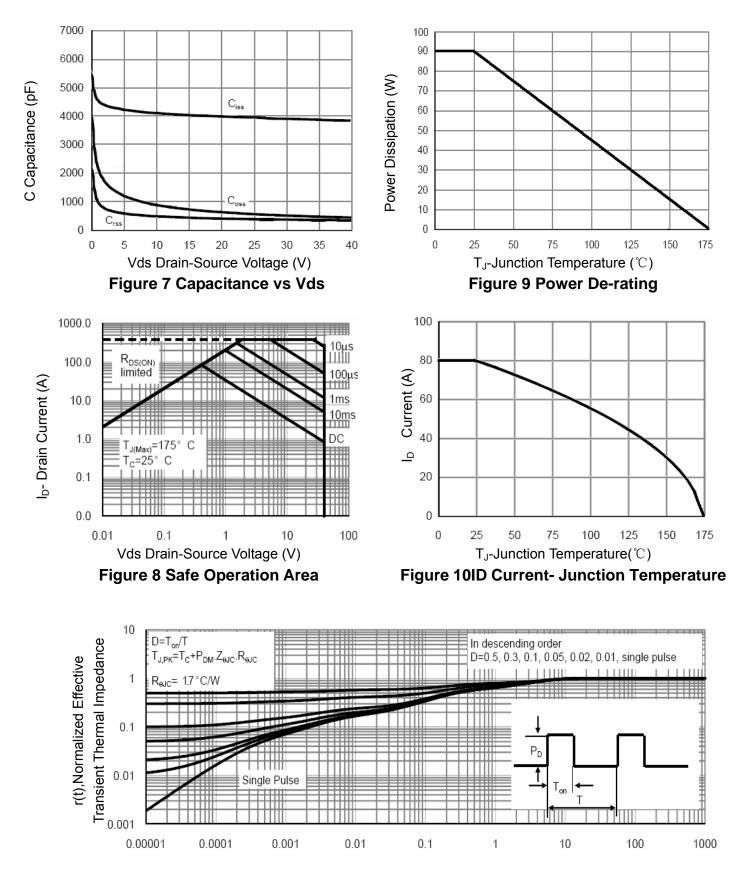
Typical Electrical and Thermal Characteristics (Curves)





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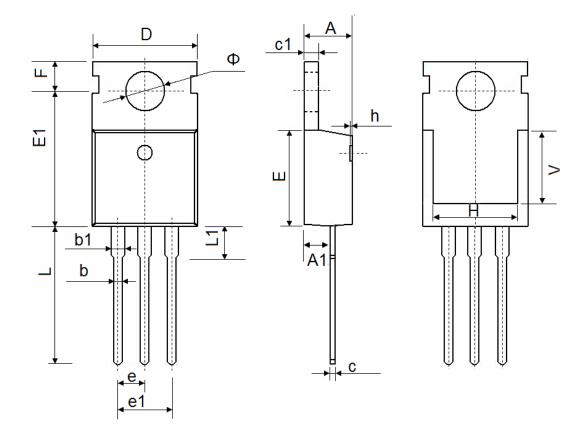
Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-220-3L Package Information



Symbol	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
e	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	





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